International Rectifier
AN INFINEON TECHNOLOGIES COMPANY

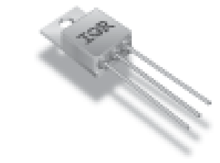
PD-95837B

2N7599T3
IRHY67C30CM
600V, N-CHANNEL
R6 TECHNOLOGY

RADIATION HARDENED POWER MOSFET THRU-HOLE (TO-257AA)

Product Summary

Part Number	Radiation Level	$R_{DS(on)}$	I_D
IRHY67C30CM	100K Rads (Si)	3.0Ω	3.4A
IRHY63C30CM	300K Rads (Si)	3.0Ω	3.4A



TO-257AA

International Rectifier's R6™ technology provides superior power MOSFETs for space applications. These devices have improved immunity to Single Event Effect (SEE) and have been characterized for useful performance with Linear Energy Transfer (LET) up to 90MeV/(mg/cm^2).

Their combination of very low $R_{DS(on)}$ and faster switching times reduces power loss and increases power density in today's high speed switching applications such as DC-DC converters and motor controllers. These devices retain all of the well established advantages of MOSFETs such as voltage control, ease of paralleling and temperature stability of electrical parameters.

Features:

- Low $R_{DS(on)}$
- Fast Switching
- Single Event Effect (SEE) Hardened
- Low Total Gate Charge
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Ceramic Eyelets
- Electrically Isolated
- Light Weight
- ESD Rating: Class 2 per MIL-STD-750, Method 1020

Absolute Maximum Ratings

Pre-Irradiation

	Parameter		Units
I_D @ V_{GS} = 12V, T_C = 25°C	Continuous Drain Current	3.4	A
I_D @ V_{GS} = 12V, T_C = 100°C	Continuous Drain Current	2.1	
I_{DM}	Pulsed Drain Current ①	13.6	
P_D @ T_C = 25°C	Max. Power Dissipation	75	W
	Linear Derating Factor	0.6	W/°C
V_{GS}	Gate-to-Source Voltage	±20	V
E_{AS}	Single Pulse Avalanche Energy ②	97	mJ
I_{AR}	Avalanche Current ①	3.4	A
E_{AR}	Repetitive Avalanche Energy ①	7.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	8.1	V/ns
T_J T_{STG}	Operating Junction Storage Temperature Range	-55 to 150	°C
	Lead Temperature	300 (0.063 in. /1.6 mm from case for 10s)	
	Weight	4.3 (Typical)	g

For footnotes refer to the last page

08/05/15

Electrical Characteristics @ Tj = 25°C (Unless Otherwise Specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	600	—	—	V	V_{GS} = 0V, I_D = 1.0mA
$\Delta BV_{DSS}/\Delta T_J$	Temperature Coefficient of Breakdown Voltage	—	0.51	—	V/°C	Reference to 25°C, I_D = 1.0mA
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance	—	—	3.0	Ω	V_{GS} = 12V, I_D = 2.1A ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	V_{DS} = V_{GS}, I_D = 1.0mA
g_{fs}	Forward Transconductance	3.7	—	—	S	V_{DS} = 15V, I_{DS} = 2.1A ④
I_{DSS}	Zero Gate Voltage Drain Current	—	—	10	µA	V_{DS} = 480V ,V_{GS} = 0V
		—	—	25		V_{DS} = 480V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	V_{GS} = 20V
I_{GSS}	Gate-to-Source Leakage Reverse	—	—	-100		V_{GS} = -20V
Q_g	Total Gate Charge	—	—	35	nC	V_{GS} =12V, I_D = 3.4A
Q_{gs}	Gate-to-Source Charge	—	—	12		V_{DS} = 300V
Q_{gd}	Gate-to-Drain ('Miller') Charge	—	—	15		
$t_{d(on)}$	Turn-On Delay Time	—	—	18	ns	V_{DD} = 300V, I_D = 3.4A
t_r	Rise Time	—	—	12		V_{GS} =12V, R_G = 7.5Ω
$t_{d(off)}$	Turn-Off Delay Time	—	—	36		
t_f	Fall Time	—	—	14		
$L_S + L_D$	Total Inductance	—	6.8	—	nH	Measured from Drain lead (6mm / 0.25in. from package) to Source lead (6mm /0.25in. from package)
C_{iss}	Input Capacitance	—	1267	—	pF	V_{GS} = 0V, V_{DS} = 25V
C_{oss}	Output Capacitance	—	79	—		f = 1.0MHz
C_{rss}	Reverse Transfer Capacitance	—	1.1	—		
R_g	Internal Gate Resistance	—	1.1	—	Ω	f = 1.0MHz, open drain

Source-Drain Diode Ratings and Characteristics

	Parameter	Min	Typ	Max	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	3.4	A	
I_{SM}	Pulse Source Current (Body Diode) ①	—	—	13.6		
V_{SD}	Diode Forward Voltage	—	—	1.2	V	T_j = 25°C, I_S = 3.4A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	—	—	741	ns	T_j = 25°C, I_F = 3.4A, di/dt ≤ 100A/µs
Q_{RR}	Reverse Recovery Charge	—	—	2.1	nC	V_{DD} ≤ 50V ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				

Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R_{thJC}	Junction-to-Case	—	—	1.67	°C/W	
R_{thJA}	Junction-to-Ambient	—	—	80		Typical Socket Mount

Note: Corresponding Spice and Saber models are available on International Rectifier Web site.

For footnotes refer to the last page

International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table 1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation ⑤⑥

	Parameter	Up to 300K Rads (Si)[1]		Units	Test Conditions
		Min	Max		
BV_{DSS}	Drain-to-Source Breakdown Voltage	600	—	V	$V_{GS} = 0V$, $I_D = 1.0mA$
$V_{GS(th)}$	Gate Threshold Voltage	2.0	4.0		$V_{GS} = V_{DS}$, $I_D = 1.0mA$
I_{GSS}	Gate-to-Source Leakage Forward	—	100	nA	$V_{GS} = 20V$
I_{GSS}	Gate-to-Source Leakage Reverse	—	-100		$V_{GS} = -20V$
I_{DSS}	Zero Gate Voltage Drain Current	—	10	µA	$V_{DS}= 480V$, $V_{GS}= 0V$
$R_{DS(on)}$	Static Drain-to-Source ④ On-State Resistance (TO-3)	—	2.9	Ω	$V_{GS} = 12V$, $I_D = 2.1A$
V_{SD}	Diode Forward Voltage ④	—	1.2	V	$V_{GS} = 0V$, $I_D = 3.4A$

1. Part numbers: IRHY67C30CM and IRHY63C30CM

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Typical Single Event Effect Safe Operating Area

Ion	LET	Energy	Range	VDS (V)			
	(MeV/(mg/cm^2))	(MeV)	(µm)	@VGS = 0V	@VGS = -4V	@VGS = -12V	@VGS = - 20V
Kr	32.4	679	83.3	600	600	600	600
Xe	56.2	1060	83.5	600	600	600	-
Au	89.5	1555	84	600	600	-	-

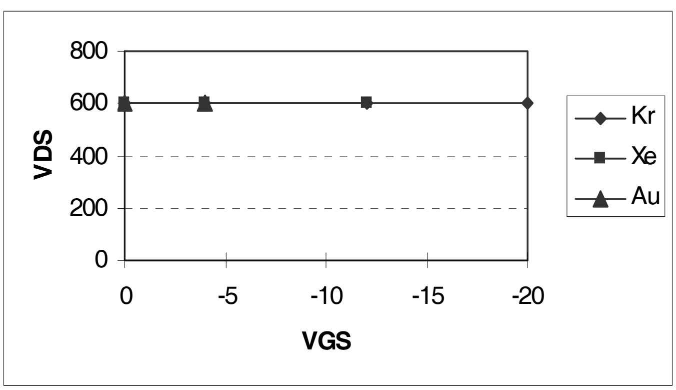


Fig a. Typical Single Event Effect, Safe Operating Area

For footnotes refer to the last page

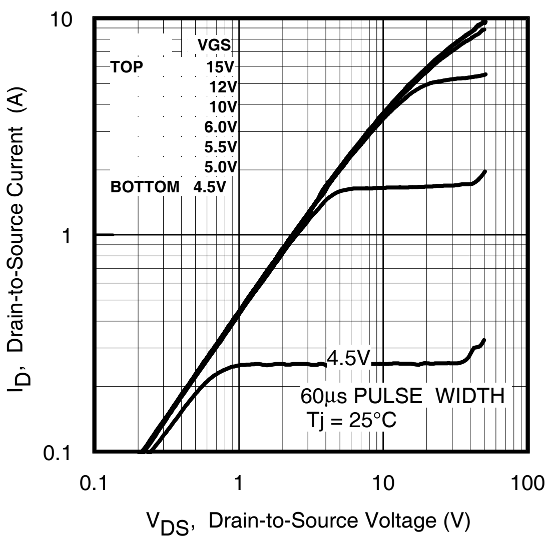


Fig 1. Typical Output Characteristics

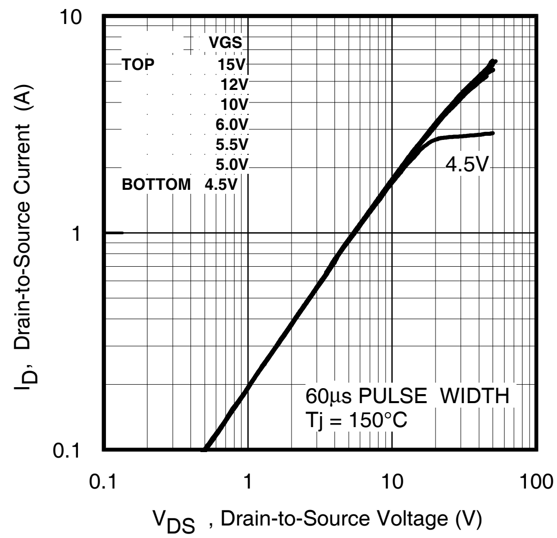


Fig 2. Typical Output Characteristics

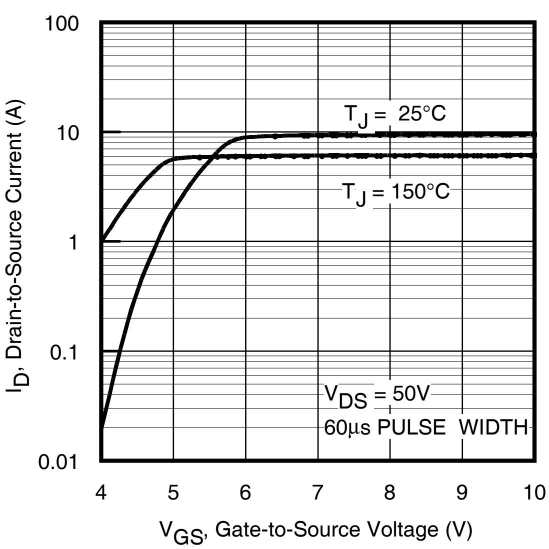


Fig 3. Typical Transfer Characteristics

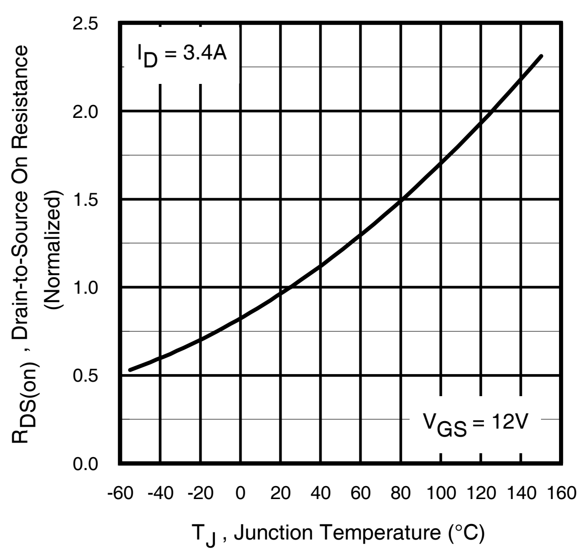


Fig 4. Normalized On-Resistance Vs. Temperature

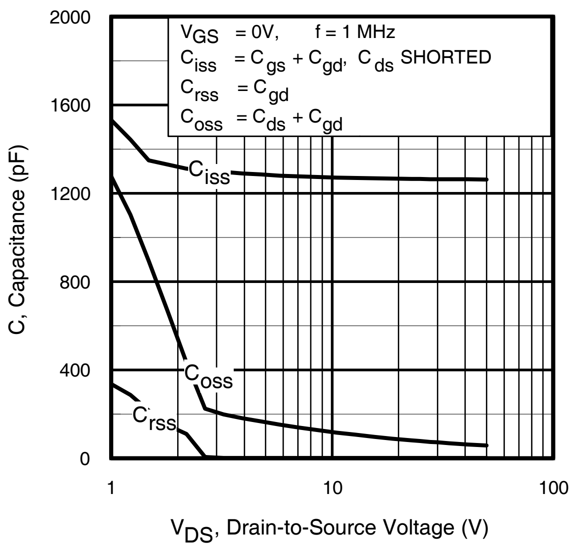


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

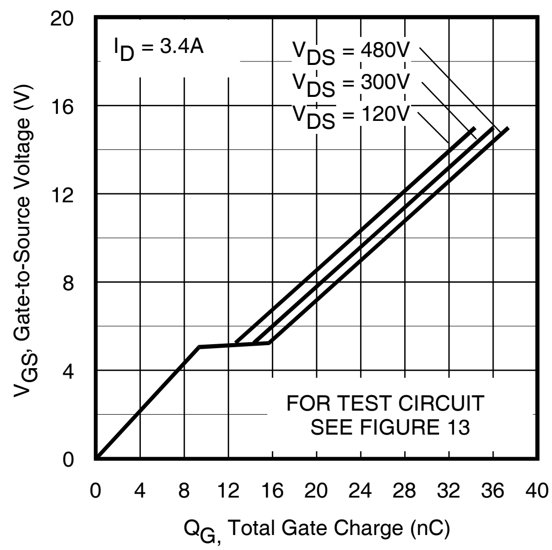


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

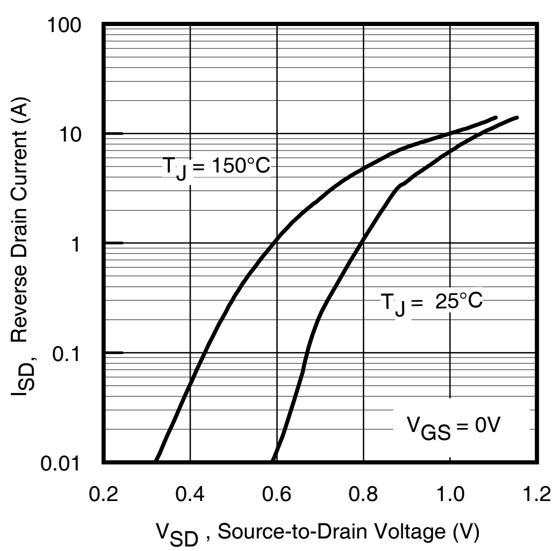


Fig 7. Typical Source-Drain Diode Forward Voltage

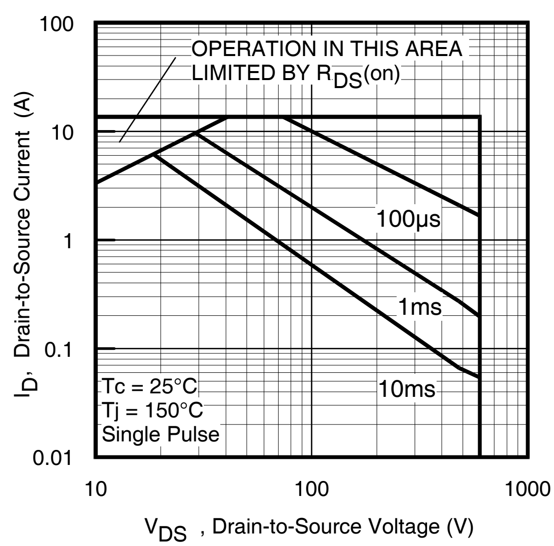


Fig 8. Maximum Safe Operating Area

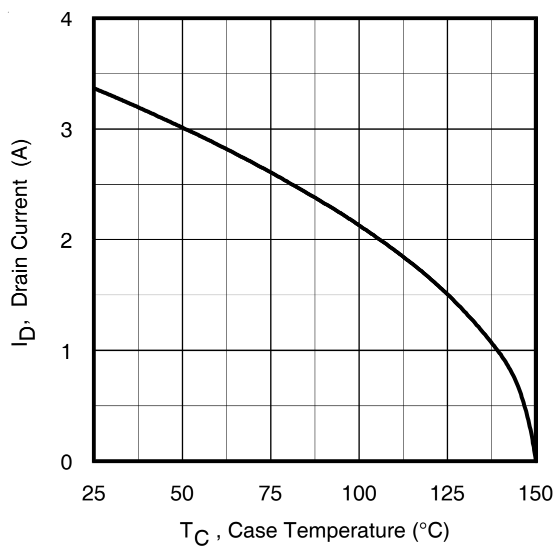


Fig 9. Maximum Drain Current Vs. Case Temperature

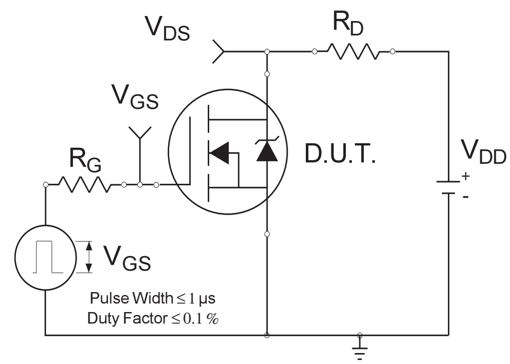


Fig 10a. Switching Time Test Circuit

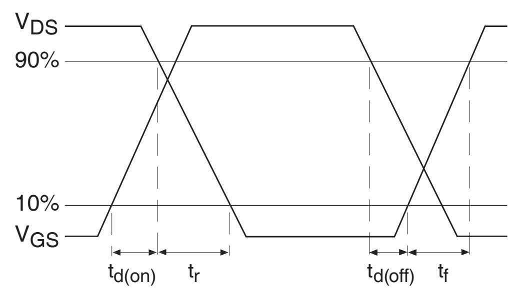


Fig 10b. Switching Time Waveforms

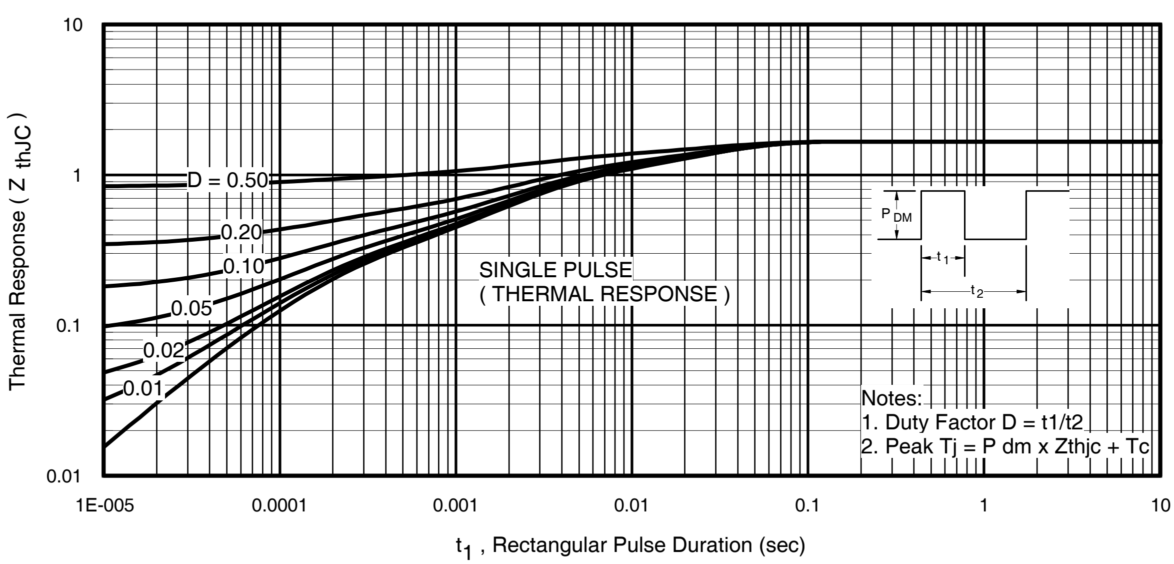


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

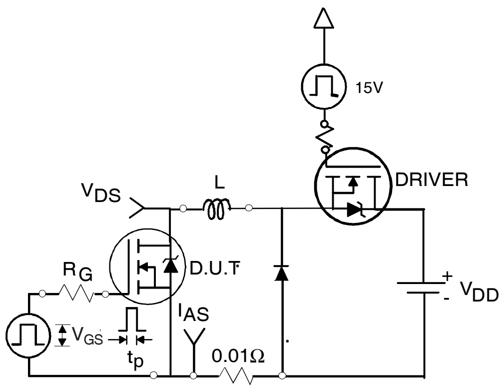


Fig 12a. Unclamped Inductive Test Circuit

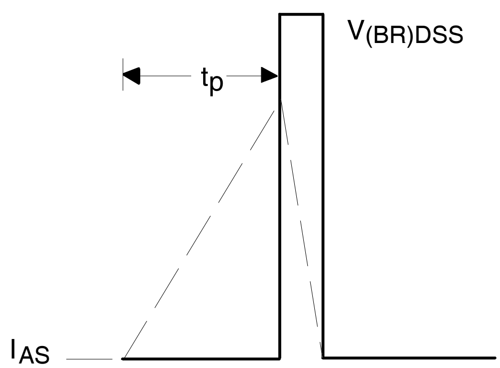


Fig 12b. Unclamped Inductive Waveforms

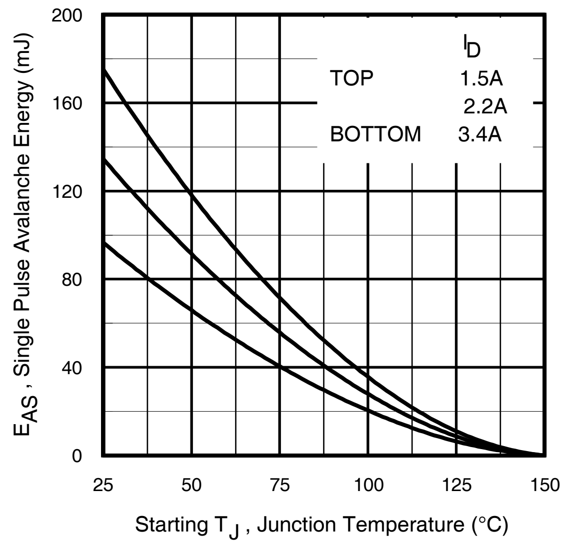


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

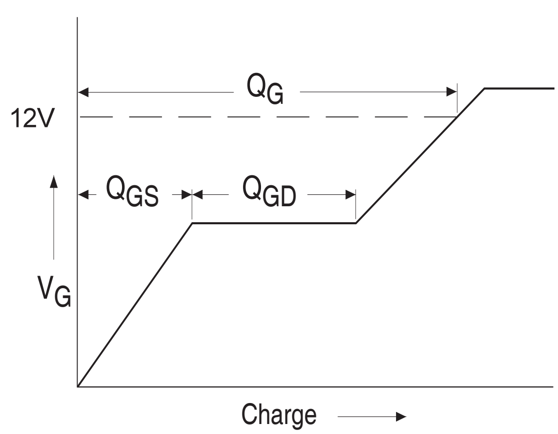


Fig 13a. Basic Gate Charge Waveform

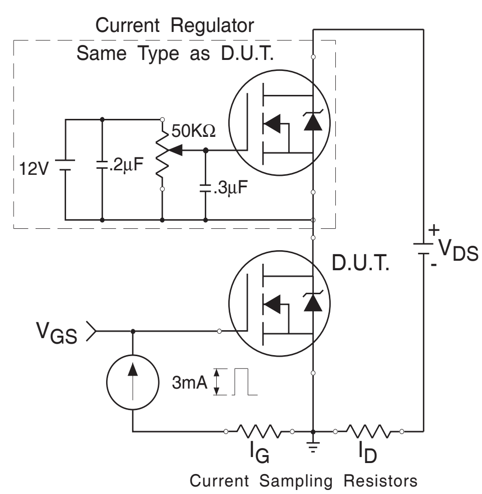


Fig 13b. Gate Charge Test Circuit

Footnotes:

① Repetitive Rating; Pulse width limited by maximum junction temperature.

② V_{DD} = 50V, starting T_J = 25°C, L = 16.7mH Peak I_L = 3.4A, V_{GS} = 12V

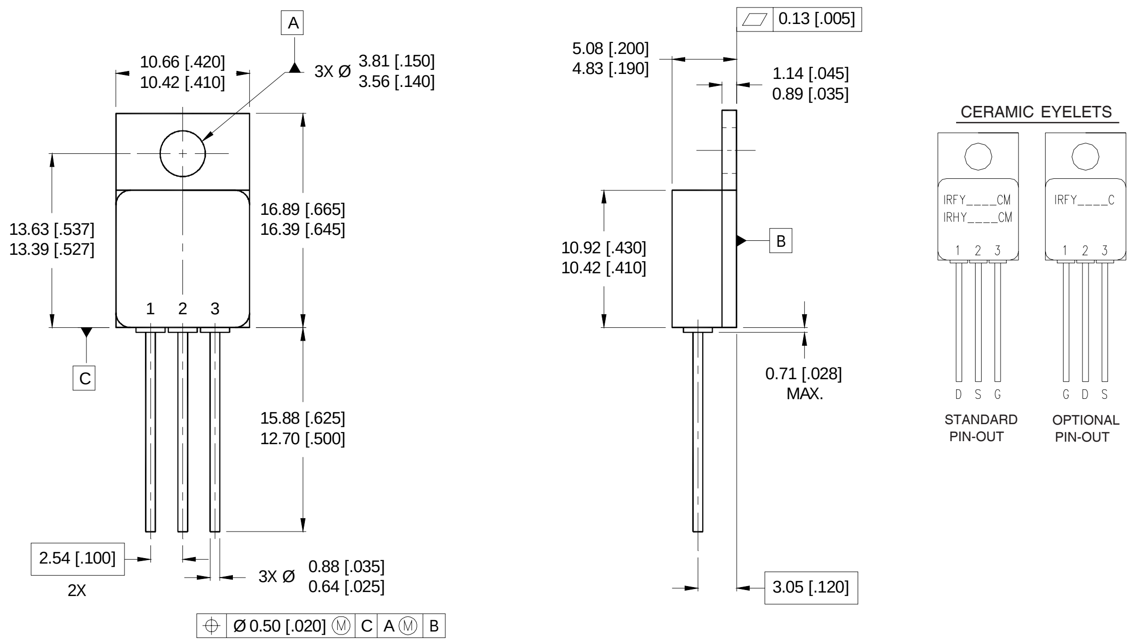
③ $I_{SD} \leq$ 3.4A, di/dt $\leq$ 560A/µs, $V_{DD} \leq$ 600V, $T_J \leq$ 150°C

④ Pulse width $\leq$ 300 µs; Duty Cycle $\leq$ 2%

⑤ **Total Dose Irradiation with V_{GS} Bias.** 12 volt V_{GS} applied and V_{DS} = 0 during irradiation per MIL-STD-750, method 1019, condition A.

⑥ **Total Dose Irradiation with V_{DS} Bias.** 480 volt V_{DS} applied and V_{GS} = 0 during irradiation per MIL-STD-750, method 1019, condition A.

Case Outline and Dimensions — TO-257AA



NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE TO-257AA.

PIN ASSIGNMENTS

1 = DRAIN
2 = SOURCE
3 = GATE

CAUTION

BERYLLIA WARNING PER MIL-PRF-19500

Package containing beryllia shall not be ground, sandblasted, machined, or have other operations performed on them which will produce beryllia or beryllium dust. Furthermore, beryllium oxide packages shall not be placed in acids that will produce fumes containing beryllium.

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